SENSITRON

SEMICONDUCTOR

MURC1060

Technical Data Data Sheet 4860, Rev.-

MURC1060 Ultrafast Silicon Die

Applications:

• Switching Power Supply • General Purpose • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Glass-Passivated
- Epitaxial Construction.
- Low Reverse Leakage Current
- High Surge Current Capability
- Low Forward Voltage Drop
- Fast Reverse-Recovery Behavior

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V _{RWM}	-	600	V
Max. Average Forward	I _{F(AV)}	50% duty cycle @T _C =100°C, rectangular wave form	10	A
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse	60	A
Max. Junction Capacitance	CJ	@V _R = 5V, T _C = 25 °C f_{SIG} = 1MHz, V _{SIG} = 50mV (p-p)	240	pF
Max. Junction Temperature	TJ	-	-65 to +150	°C
Max. Storage Temperature	T _{stg}	-	-65 to +150	°C

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop *	V _{F1}	@ 10A, Pulse, T _J = 25 °C	2.2	V
	V _{F2}	@ 10A, Pulse, T _J = 100 °C	2.0	V
Max. Reverse Current *	I _{R1}	@V _R = rated V _R T _J = 25 °C	5	μA
	I _{R2}	@V _R = 0.8V _R T _J = 100 °C	50	μA
Max Reverse Recovery Time	t _{rr}	I _F =0.5A, I _R =1.0A, I _{REC} =0.25A	50	nS
Max Reverse Recovery Time	t _{rr}	I _F =10A, di/dt=200A/μs	90	nS

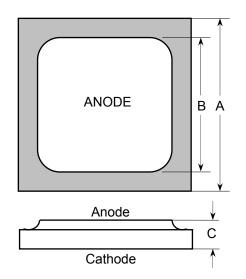
* Pulse Width < 300µs, Duty Cycle <2%

SENSITRON

SEMICONDUCTOR

Technical Data Data Sheet 4860, Rev.-

Dimensions in inches (mm)



Top side metalization: AI - 25 kÅ minimum or Ti/Ni/Ag - 30 kÅ minimum Bottom side metalization: Ti/Ni/Ag - 30 kÅ minimum. Bottom side is cathode, top side is anode.

Die type	Area (mil ²)	Dimension A ⁽¹⁾	Dimension B ⁽¹⁾	Dimension C ⁽²⁾
		Inch (millimeter)	Inch (millimeter)	Inch (millimeter)
Si p-n die	85 x 85	0.085 (2.159)	0.069 (1.753)	0.009 (0.229)
(1) - 1	000" (0 070)			

⁽¹⁾ Tolerance is ± 0.003" (0.076 mm) ⁽²⁾ Tolerance is ± 0.001" (0.025 mm)

DISCLAIMER:

1- The information given herein, including the specifications and dimensions, is subject to change without prior notice to improve product characteristics. Before ordering, purchasers are advised to contact the Sensitron Semiconductor sales department for the latest version of the datasheet(s).

2- In cases where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, medical equipment, and safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of users' fail-safe precautions or other arrangement .

3- In no event shall Sensitron Semiconductor be liable for any damages that may result from an accident or any other cause during operation of the user's units according to the datasheet(s). Sensitron Semiconductor assumes no responsibility for any intellectual property claims or any other problems that may result from applications of information, products or circuits described in the datasheets.

4- In no event shall Sensitron Semiconductor be liable for any failure in a semiconductor device or any secondary damage resulting from use at a value exceeding the absolute maximum rating.

5- No license is granted by the datasheet(s) under any patents or other rights of any third party or Sensitron Semiconductor.

6- The datasheet(s) may not be reproduced or duplicated, in any form, in whole or part, without the expressed written permission of Sensitron Semiconductor.

7- The products (technologies) described in the datasheet(s) are not to be provided to any party whose purpose in their application will hinder maintenance of international peace and safety nor are they to be applied to that purpose by their direct purchasers or any third party. When exporting these products (technologies), the necessary procedures are to be taken in accordance with related laws and regulations.

• 221 West Industry Court 🗉 Deer Park, NY 11729-4681 🗏 (631) 586-7600 FAX (631) 242-9798 • World Wide Web Site - http://www.sensitron.com • E-Mail Address - sales@sensitron.com •

Technical Data Data Sheet 4860, Rev.-

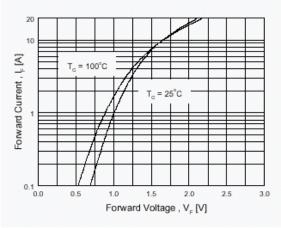


Figure 1. Typical Forward Voltage Drop vs. Forward Current

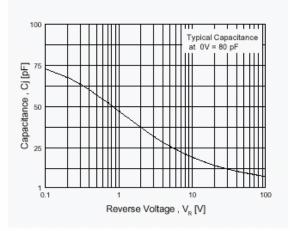


Figure 3. Typical Junction Capacitance

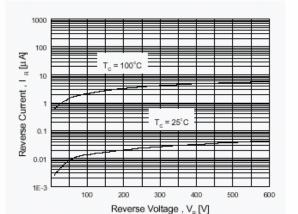


Figure 2. Typical Reverse Current vs. Reverse Voltage

